G. Device & Process Modeling, Simulation and Reliability 분과

[TJ1-G] Device Physics & Simulation

Date	Feb. 25, 2014 (Tue.)
Place	Room J / 제1공학관 501호 (# 501, Engineering Building I)

Session Chair: 김대환 교수(국민대학교), 이상기 박사(동부하이텍)

TJ1-G-1 **09:30-10:00** **Recent Advances in Deterministic Solvers for the Boltzmann Transport Equation and Future Research Directions**
저자: Sung-Min Hong
소속: School of Information and Communications, Gwangju Institute of Science and Technology

TJ1-G-2 **10:00-10:15** **Simulation of III-V UTB SB-MOSFETs using Tight-Binding Band-Structure Calculations**
저자: Howon Choi, Jaehyun Lee, Yolum Lee, and Mincheol Shin
소속: Department of Electrical Engineering, KAIST

TJ1-G-3 **10:15-10:30** **3D Simulation of Threshold Voltage Variations Due to Random Grain Boundary and Discrete Dopants in Sub-20 nm Gate-All-Around Poly-Si Transistors**
저자: Jungsik Kim[1], Hyeongwan Oh[3], Junyoung Lee[3], Jiwon Kim[3], Chang-Ki Baek[2], and Jeong-Soo Lee[1,3]
소속: [1]Department of IT Convergence Engineering, Pohang University of Science and Technology, [2]Creative IT Engineering and Future IT Innovation Lab, Pohang University of Science and Technology, [3]Electrical Engineering, Pohang University of Science and Technolog

TJ1-G-4 **10:30-10:45** **Simulation of Dual Material Gate InAs Schottky Barrier Field Effect Transistor**
저자: Wonchul Choi, Jaehyun Lee, and Mincheol Shin
소속: Department of Electrical Engineering, KAIST